

Contents of

Applied Physics A 60

Materials Science & Processing

This listing presents the papers in alphabetical order of the first author. The Author Index that follows covers Volume 60 of *Applied Physics A* and *B*, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second and third columns contain the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The PACS numbers given in the fourth column may be used in conjunction with the PACS listing on the left to infer the topic of a paper. The articles the pages of which are characterized by S in the Author Index have been published in the supplement of Volume 60/2&3.

Abdallah M.H., Ramaden Y., Jawad S.A., Hassan M., Ahmad M.S., Zihlif A.M.:

Effect of annealing on the electrical properties and refractive index of HgI_2 single crystals.

Appl. Phys. A 60/5, 437-440 (1995) PACS: 72.20 78.20

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Aussenegg F.R., Leitner A., Gold H.:

Optical second-harmonic generation on metal-island films.

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Bala P., Bala W.:

Tunneling in double-barrier ZnSe/ZnTe structures: Time-dependent analysis.

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SHG studies of magnetization effects on polycrystalline nickel surfaces.

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Bor Z., Racz B., Szabo G., Xenakis D., Kalpouzos C., Fotakis C.:

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Brozel M.R.:

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Brune H., Röder H., Romainczyk Ch., Boragno C., Kern K.:

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Luminescence centers in porous silicon.

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